

Title (en)

METHOD AND DEVICE FOR DEPOSITING SILICON ON A SUBSTRATE

Title (de)

VERFAHREN UND VORRICHTUNG ZUR ABSCHIEDUNG VON SILIZIUM AUF EINEM SUBSTRAT

Title (fr)

PROCÉDÉ ET DISPOSITIF POUR DÉPOSER DU SILICIUM SUR UN SUBSTRAT

Publication

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Application

EP 11811328 A 20111223

Priority

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Abstract (en)

[origin: WO2012084261A1] The invention relates to a method for depositing silicon on a substrate (32) using a focused beam of charged particles (14). A precursor (20) containing silicon is provided, said precursor being dissociated by the beam (14) in the immediate vicinity of the substrate (32). The aim of the invention is to allow the deposition of silicon on a substrate (32) in a particularly effective, material-protecting, and precise manner. For this purpose, a polysilane is used as the precursor (20).

IPC 8 full level

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Citation (search report)

See references of WO 2012084261A1

Citation (examination)

JP H0945922 A 19970214 - SHOWA DENKO KK

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DOCDB simple family (publication)

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